Product Summary

Device	BV_{DSS}	$R_{DS(ON)}$	I_D T_A = +25°C
N-Channel	20V	42mΩ @ V_{GS}= 4.5V	4.0A
		60mΩ @ V_{GS}= 2.5V	3.5A
P-Channel	-20V	70mΩ @ V_{GS}= -4.5V	-3.3A
		100mΩ @ V_{GS}= -2.5V	-2.8A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

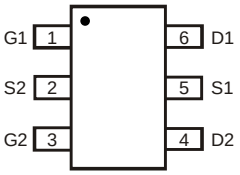
- Backlighting
- DC-DC Converters
- Power Management Functions

Mechanical Data

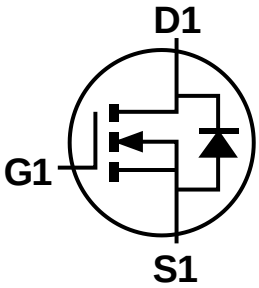
- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.013 grams (Approximate)

TSOT26

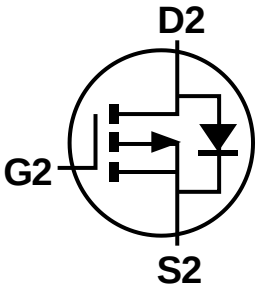
Top View



Top View



Q1 N-Channel MOSFET



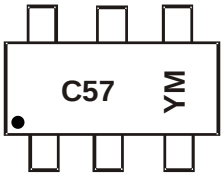
Q2 P-Channel MOSFET

Ordering Information (Note 4)

Part Number	Case	Packaging
DMC2057UVT-7	TSOT26	3000 / Tape & Reel
DMC2057UVT-13	TSOT26	10000 / Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



C57 = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: F = 2018)
M or $\overline{M}$ = Month (ex: 9 = September)

Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024	2025
Code	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Q1 Value	Q2 Value	Unit
Drain-Source Voltage			V_{DSS}	20	-20	V
Gate-Source Voltage			V_{GSS}	±12	±8	V
Continuous Drain Current (Note 6) N-Channel: V_{GS} = 4.5V P-Channel: V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	4.0 3.5	-3.3 -2.6	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	1.2	-1.3	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	25	-17	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	173	°C/W
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	108	°C/W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	37	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics Q1 N-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	µA	V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±12V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.4	—	1.2	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	32	42	mΩ	V_{GS} = 4.5V, I_D = 5.0A
			40	60		V_{GS} = 2.5V, I_D = 4.0A
			50	91		V_{GS} = 1.8V, I_D = 2.0A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	416	—	pF	V_{DS} = 10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	44	—		
Reverse Transfer Capacitance	C_{rss}	—	35	—		
Gate Resistance	R_g	—	2.0	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	4.7	—	nC	V_{DS} = 10V, I_D = 6A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	10.5	—		
Gate-Source Charge	Q_{gs}	—	0.4	—		
Gate-Drain Charge	Q_{gd}	—	1.2	—		
Turn-On Delay Time	$t_{D(ON)}$	—	2.6	—	ns	V_{DS} = 10V, V_{GS} = 4.5V, R_g = 6Ω, I_D = 6A
Turn-On Rise Time	t_R	—	3.3	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	12.2	—		
Turn-Off Fall Time	t_F	—	3.1	—		
Reverse Recovery Time	t_{RR}	—	8.3	—	ns	I_F = 6A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—	1.3	—	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

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Electrical Characteristics Q2 P-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1.0	µA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.4	—	-1.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	60	70	mΩ	V_{GS} = -4.5V, I_D = -3.5A
			73.5	100		V_{GS} = -2.5V, I_D = -3.0A
			113	160		V_{GS} = -1.8V, I_D = -2.0A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.2	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	536	—	pF	V_{DS} = -10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	78	—		
Reverse Transfer Capacitance	C_{rss}	—	69	—		
Gate Resistance	R_g	—	32	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	6.5	—	nC	V_{DS} = -4V, I_D = -3.5A
Gate-Source Charge	Q_{gs}	—	0.8	—		
Gate-Drain Charge	Q_{gd}	—	1.3	—		
Turn-On Delay Time	$t_{D(ON)}$	—	4.4	—	ns	V_{GS} = -4.5V, V_{DS} = -4V, R_g = 6Ω, R_L = 4Ω
Turn-On Rise Time	t_R	—	15.5	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	38.5	—		
Turn-Off Fall Time	t_F	—	22.2	—		
Reverse Recovery Time	t_{RR}	—	11	—	ns	I_F = -2.0A, di/dt = -100A/µs
Reverse Recovery Charge	Q_{RR}	—	2.6	—	nC	I_F = -2.0A, di/dt = -100A/µs

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

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Typical Characteristics - N-CHANNEL

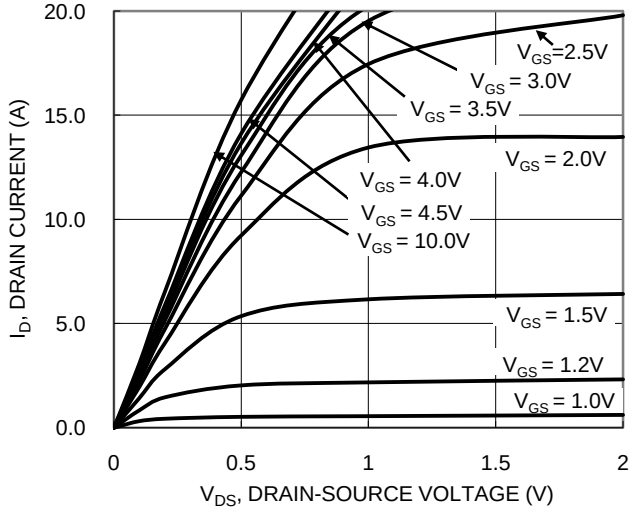

Figure 1. Typical Output Characteristic

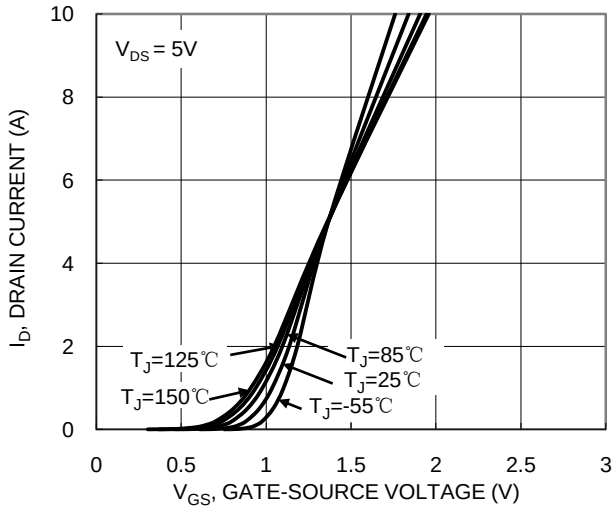

Figure 2. Typical Transfer Characteristic

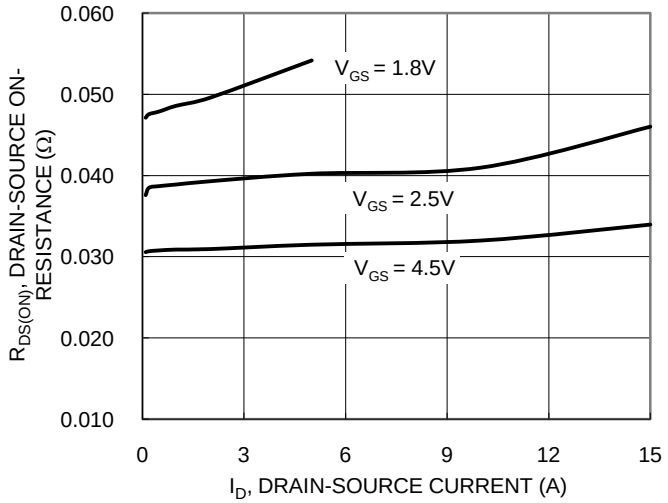

Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

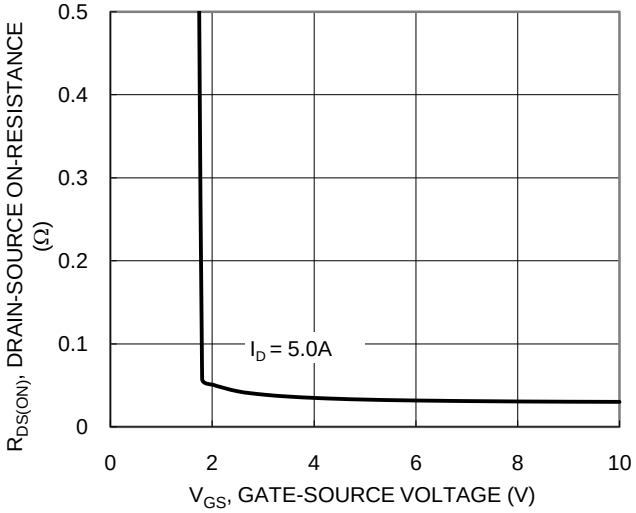

Figure 4. Typical Transfer Characteristic

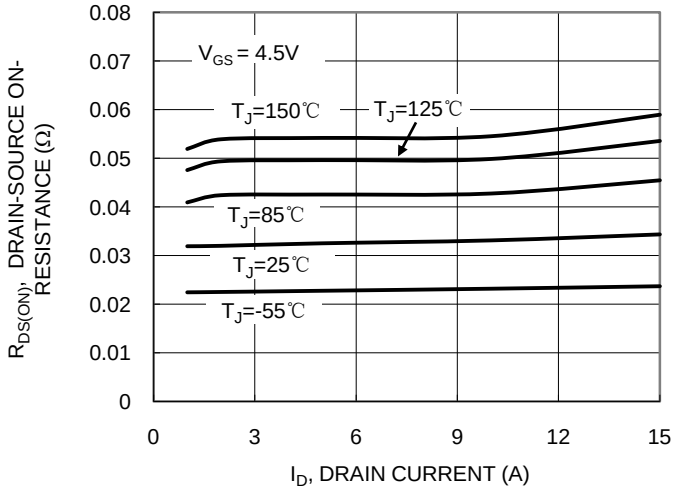

Figure 5. Typical On-Resistance vs. Drain Current and Temperature

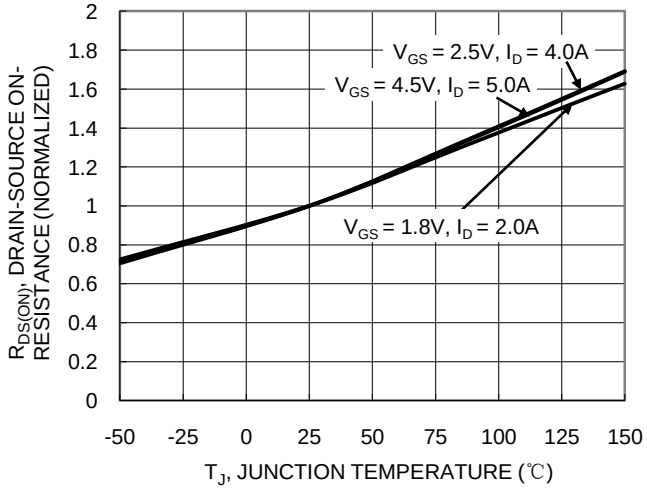

Figure 6. On-Resistance Variation with Temperature

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Typical Characteristics - N-CHANNEL (Cont.)

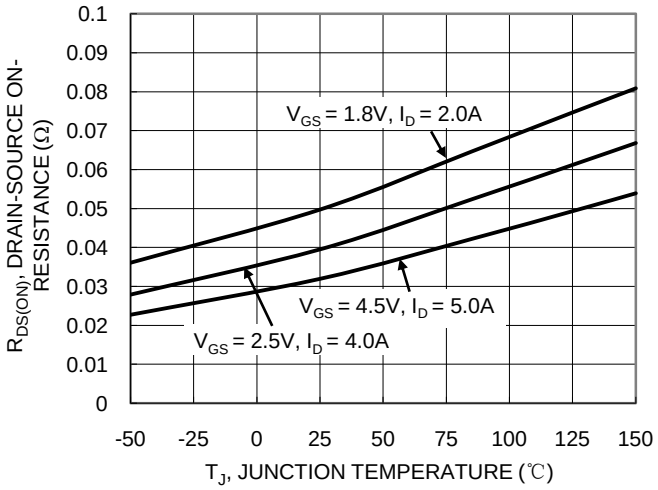

Figure 7. On-Resistance Variation with Temperature

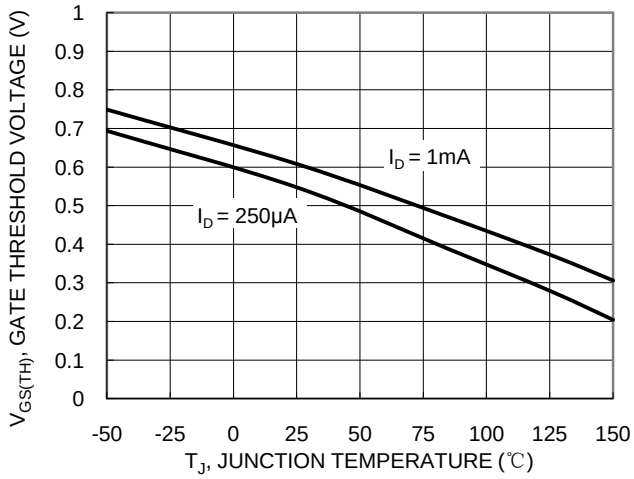

Figure 8. Gate Threshold Variation vs. Junction Temperature

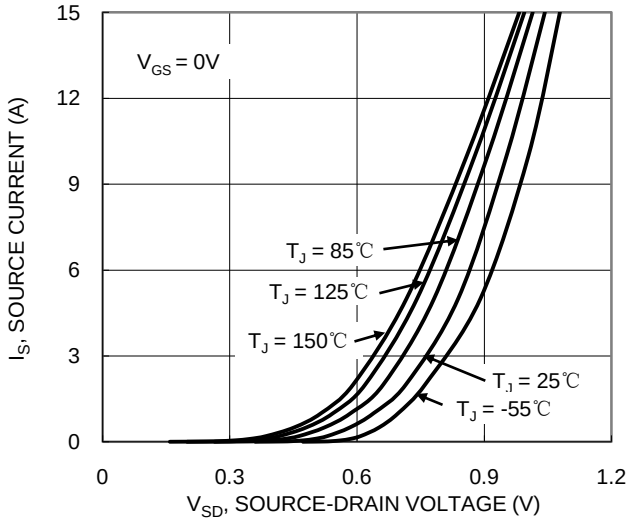

Figure 9. Diode Forward Voltage vs. Current

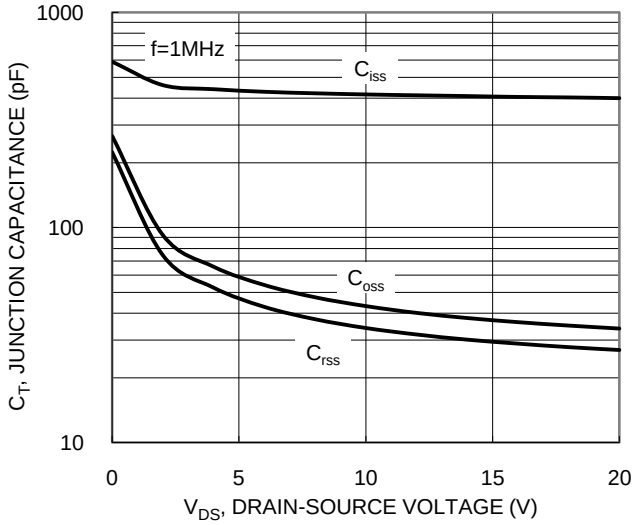

Figure 10. Typical Junction Capacitance

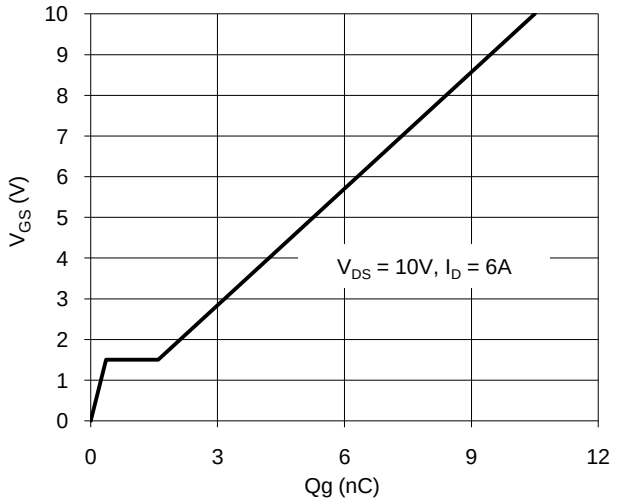

Figure 11. Gate Charge

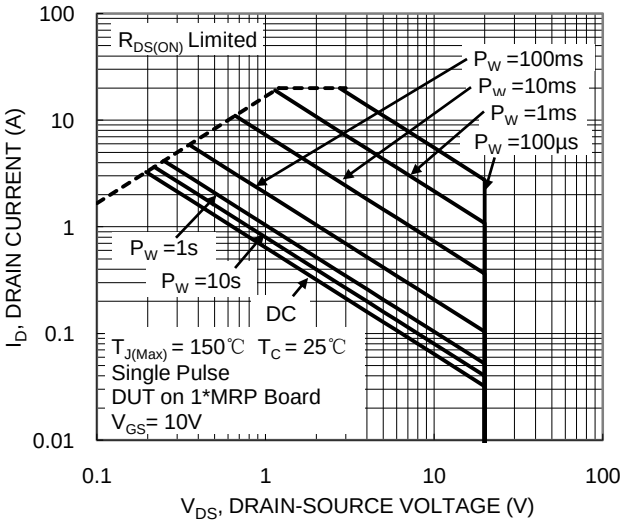

Figure 12. SOA, Safe Operation Area

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Typical Characteristics - P-CHANNEL

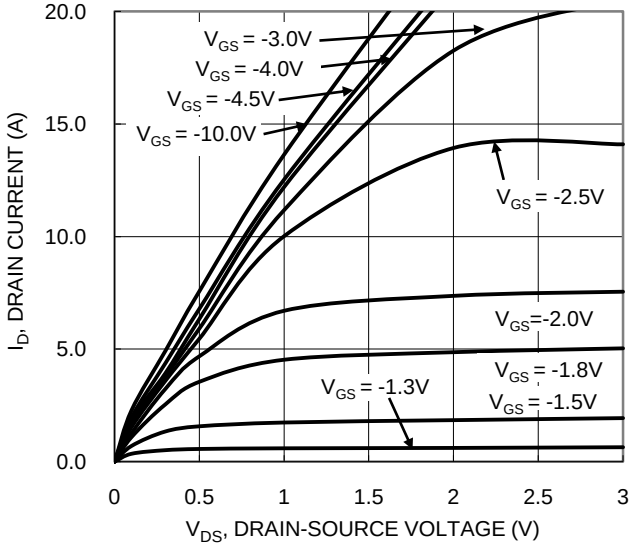

Figure 13. Typical Output Characteristic

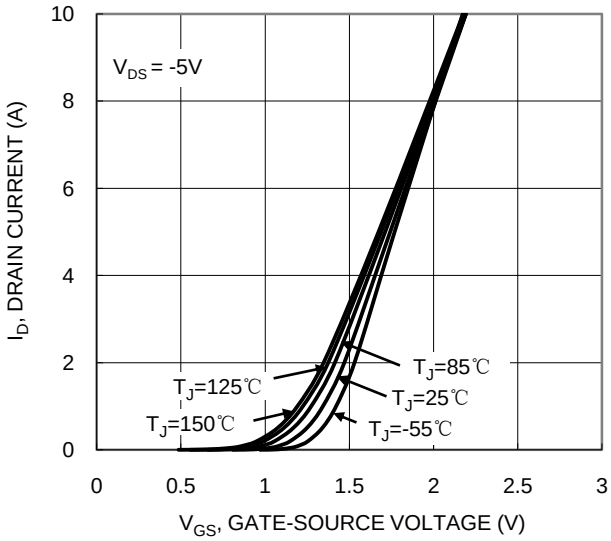

Figure 14. Typical Transfer Characteristic

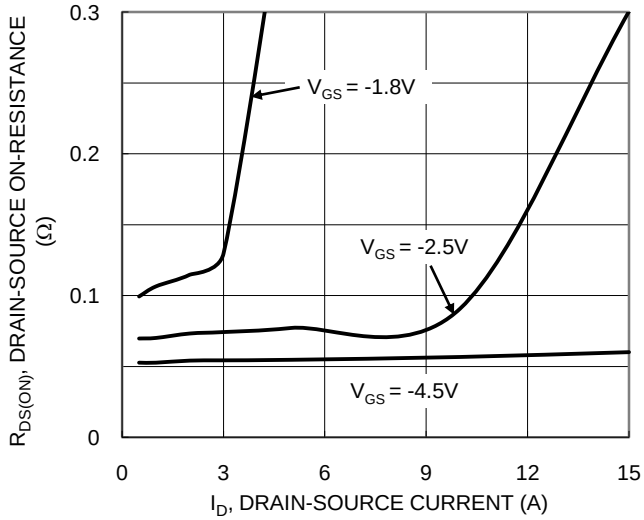

Figure 15. Typical On-Resistance vs. Drain Current and Gate Voltage

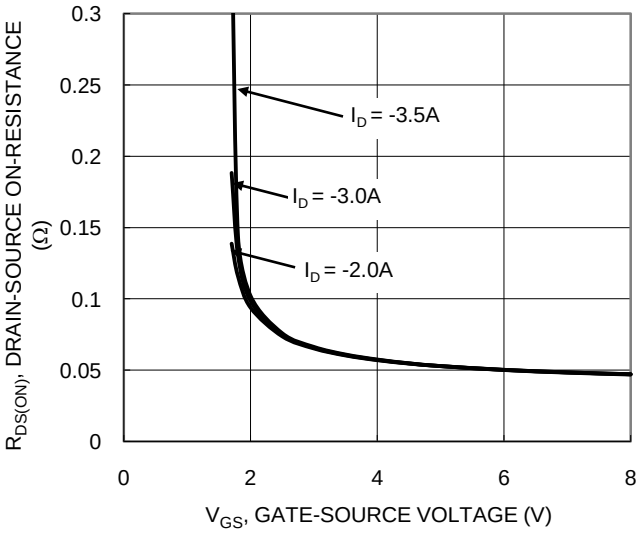

Figure 16. Typical Transfer Characteristic

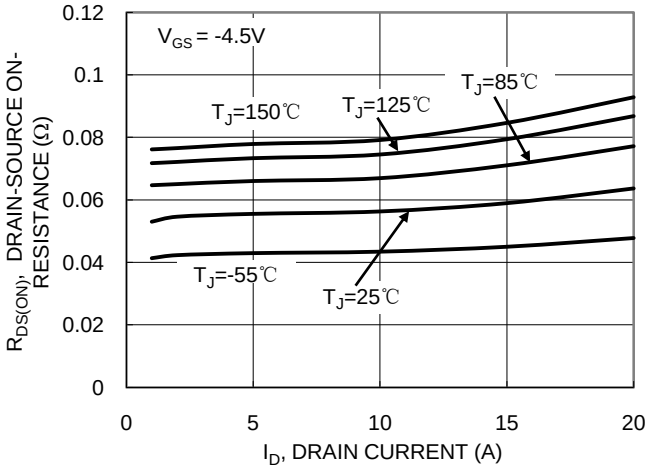

Figure 17. Typical On-Resistance vs. Drain Current and Junction Temperature

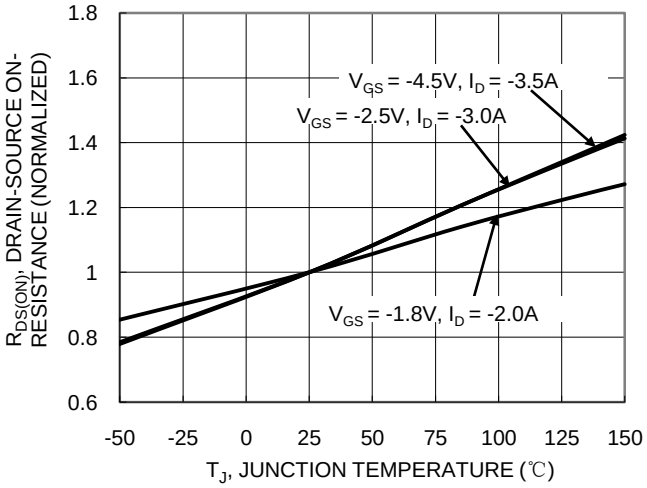

Figure 18. On-Resistance Variation with Junction Temperature

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Typical Characteristics - P-CHANNEL (Cont.)

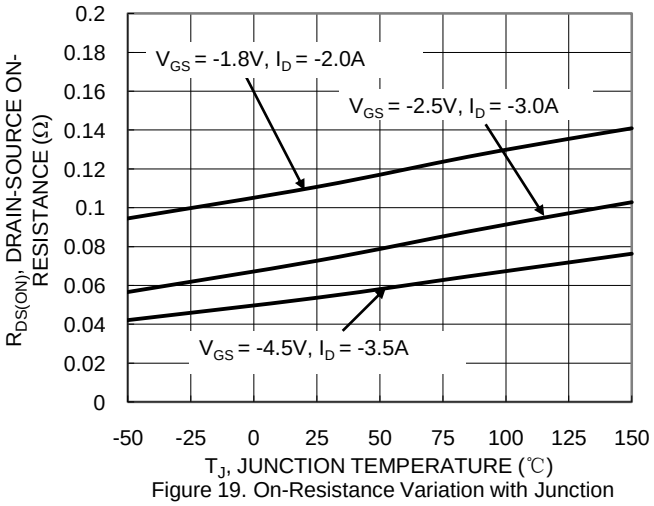

Figure 19. On-Resistance Variation with Junction Temperature

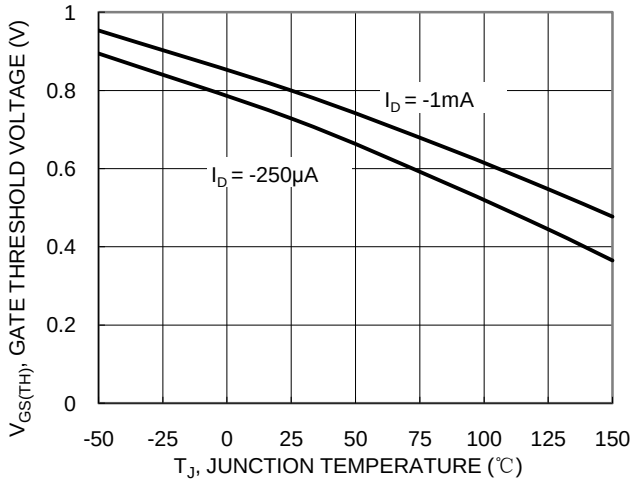

Figure 20. Gate Threshold Variation vs. Junction Temperature

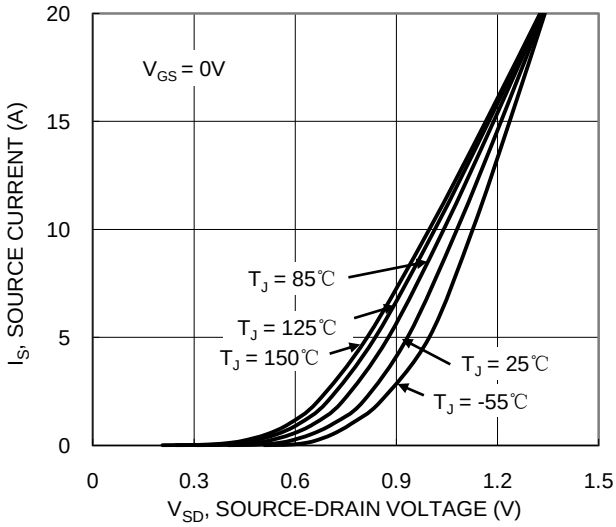

Figure 21. Diode Forward Voltage vs. Current

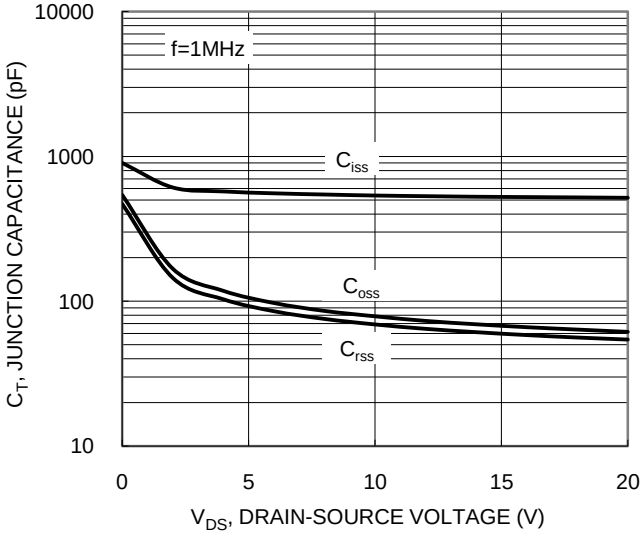

Figure 22. Typical Junction Capacitance

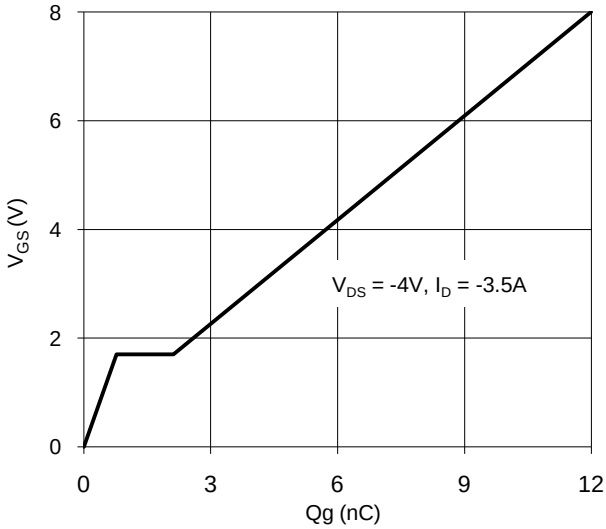

Figure 23. Gate Charge

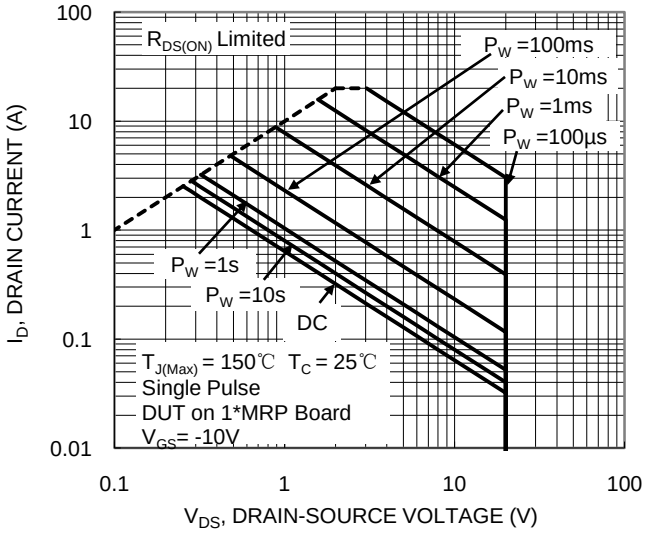

Figure 24. SOA, Safe Operation Area

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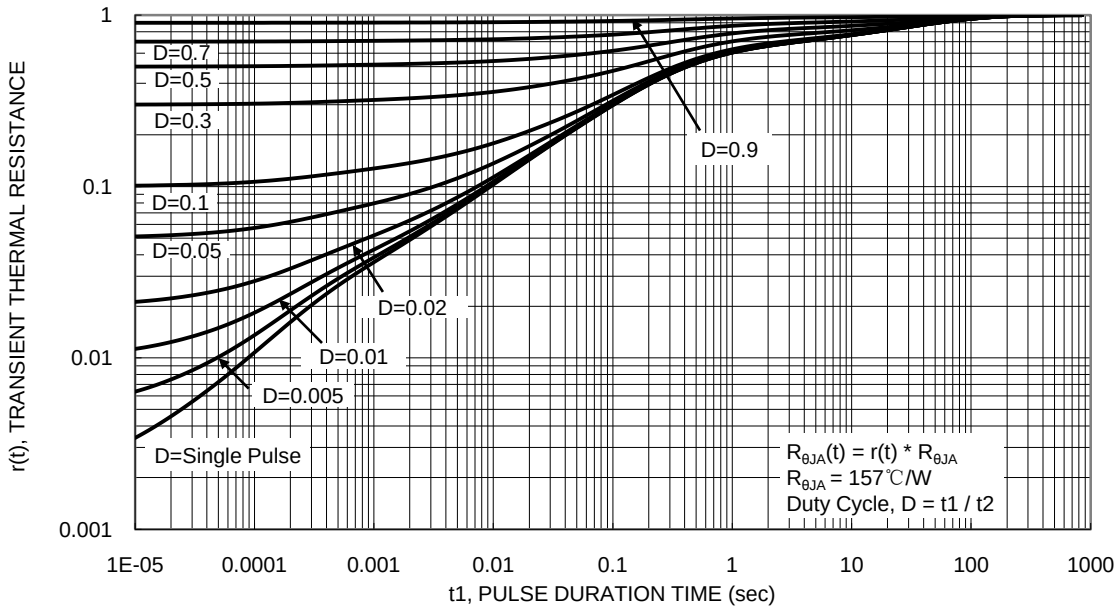

Figure 25. Transient Thermal Resistance

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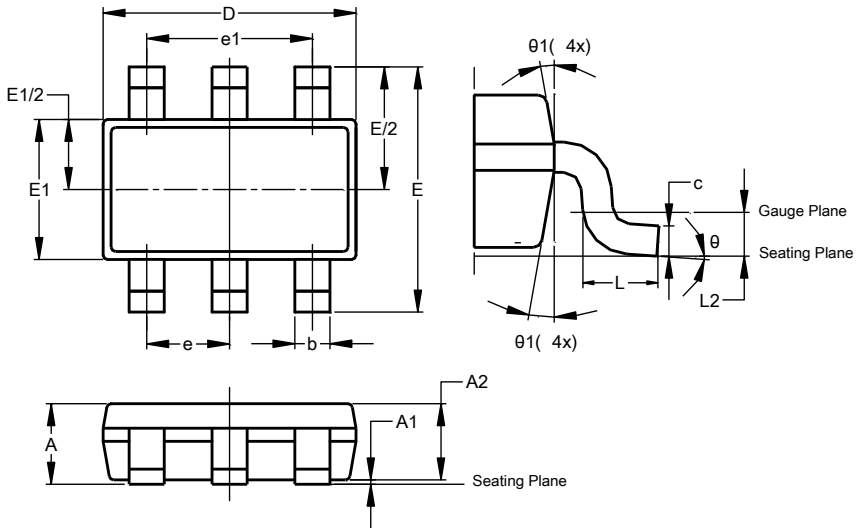
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26

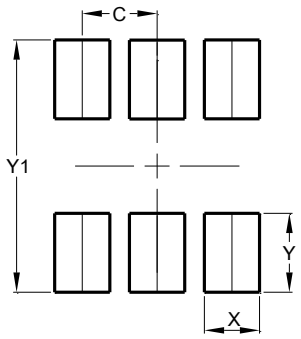


TSOT26			
Dim	**Min**	**Max**	**Typ**
A	–	1.00	–
A1	0.010	0.100	–
A2	0.840	0.900	–
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	–
c	0.120	0.200	–
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	–
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	–
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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